

2PB710ARL; 2PB710ASL 50 V, 500 mA PNP general-purpose transistors Rev. 01 – 29 October 2008 Pro

1. Product profile

1.1 General description

PNP general-purpose transistors in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

	Table	1.	Product	overview
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Type number ^[1]	Package	Package		
	NXP	JEDEC		
2PB710ARL	SOT23	TO-236AB	2PD602ARL	
2PB710ASL			2PD602ASL	
2PB710ARL/DG	SOT23	TO-236AB	2PD602ARL/DG	
2PB710ASL/DG			2PD602ASL/DG	

[1] /DG: halogen-free

1.2 Features

- General-purpose transistors
- Two current gain selections
- AEC-Q101 qualified
- Small SMD plastic package

1.3 Applications

General-purpose switching and amplification

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _C	collector current		-	-	-500	mA
h _{FE}	DC current gain	V _{CE} = -10 V; I _C = -150 mA	<u>[1]</u>			
	h _{FE} group R		120	-	240	
	h _{FE} group S		170	-	340	

[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$.



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2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline G	raphic symbol
1	base		_
2	emitter		3
3	collector		
			sym013

3. Ordering information

Type number ^[1]	Package				
	Name	Description	Version		
2PB710ARL	-	plastic surface-mounted package; 3 leads	SOT23		
2PB710ASL					
2PB710ARL/DG					
2PB710ASL/DG					

[1] /DG: halogen-free

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
2PB710ARL	SE*
2PB710ASL	SD*
2PB710ARL/DG	SU*
2PB710ASL/DG	ST*

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

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5. Limiting values

Table 6.Limiting valuesIn accordance with the Absolute Maximum Rating System (IEC 60134).							
Symbol	Parameter	Conditions	Min	Max	Unit		
V _{CBO}	collector-base voltage	open emitter	-	-60	V		
V _{CEO}	collector-emitter voltage	open base	-	-50	V		
V_{EBO}	emitter-base voltage	open collector	-	-5	V		
I _C	collector current		-	-500	mA		
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-1	A		
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms	-	-200	mA		
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW		
Tj	junction temperature		-	150	°C		
T _{amb}	ambient temperature		-55	+150	°C		
T _{stg}	storage temperature		-65	+150	°C		

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	$V_{CB} = -60 \text{ V}; \text{ I}_{E} = 0 \text{ A}$	-	-	-10	nA
	current	$\label{eq:V_CB} \begin{array}{l} V_{CB} = -60 \ V; \ I_{E} = 0 \ A; \\ T_{j} = 150 \ ^{\circ}C \end{array}$	-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; \text{ I}_{C} = 0 \text{ A}$	-	-	-10	nA
h _{FE}	DC current gain	$V_{CE} = -10 \text{ V};$ $I_{C} = -500 \text{ mA}$	<u>[1]</u> 40	-	-	
	h _{FE} group R	$V_{CE} = -10 \text{ V};$ $I_{C} = -150 \text{ mA}$	[<u>1]</u> 120	-	240	
	h _{FE} group S	$V_{CE} = -10 \text{ V};$ $I_{C} = -150 \text{ mA}$	[<u>1]</u> 170	-	340	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = -300 \text{ mA};$ $I_{\rm B} = -30 \text{ mA}$	[1] -	-	-600	mV

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{BEsat}	base-emitter saturation voltage	I _C = -300 mA; I _B = -30 mA	<u>[1]</u> _	-	-1.5	V
f _T	transition frequency	V _{CE} = -10 V; I _C = -50 mA; f = 100 MHz				
	h _{FE} group R		120	-	-	MHz
	h _{FE} group S		140	-	-	MHz
C _c	collector capacitance	$V_{CB} = -10 V;$ $I_E = i_e = 0 A;$ f = 1 MHz	-	-	15	pF

Table 8. Characteristics ...continued

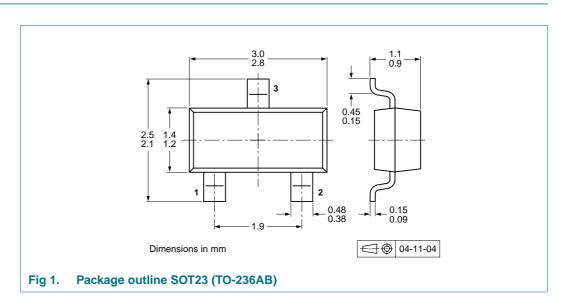
[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



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10. Packing information

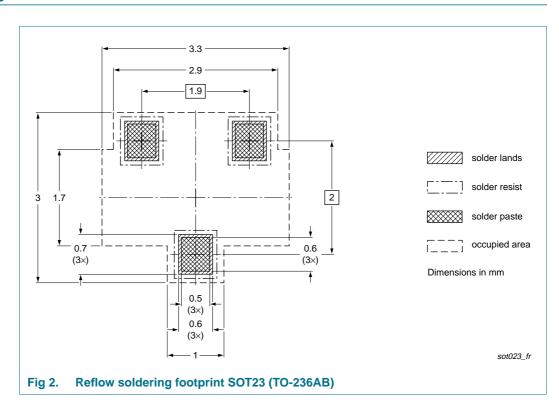
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

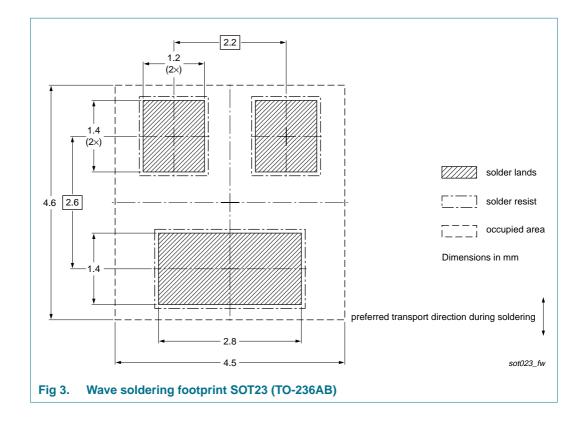
Type number ^[2]	Package	Description	Packing	Packing quantity		
			3000	10000		
2PB710ARL	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235		
2PB710ASL						
2PB710ARL/DG						
2PB710ASL/DG						

- [1] For further information and the availability of packing methods, see <u>Section 14</u>.
- [2] /DG: halogen-free

11. Soldering



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2PB710AXL_1
Product data sheet

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12. Revision history

Table 10. Revision history						
Document ID	Release date	Data sheet status	Change notice	Supersedes		
2PB710AXL_1	20081029	Product data sheet	-	-		

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13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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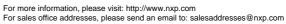
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